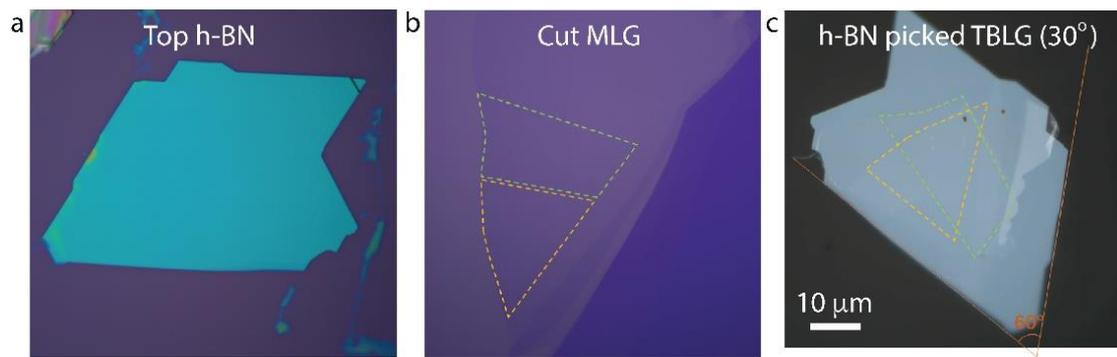


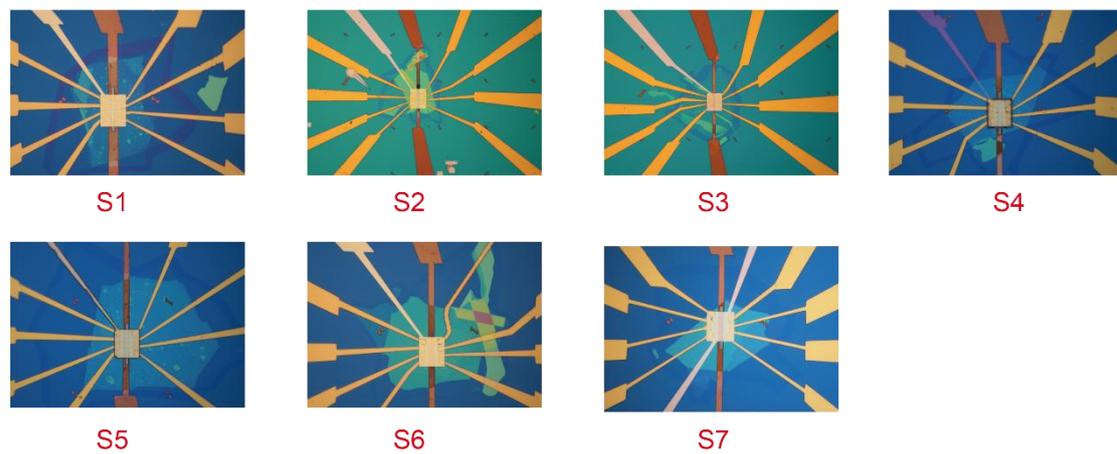
**Supplementary Information for**  
**Ferroelectric Polarization in an h-BN-Encapsulated 30°-Twisted**  
**Bilayer–Graphene Heterostructure**

Lingling Ren,<sup>1,2</sup> Baojuan Dong<sup>1,2,\*</sup>

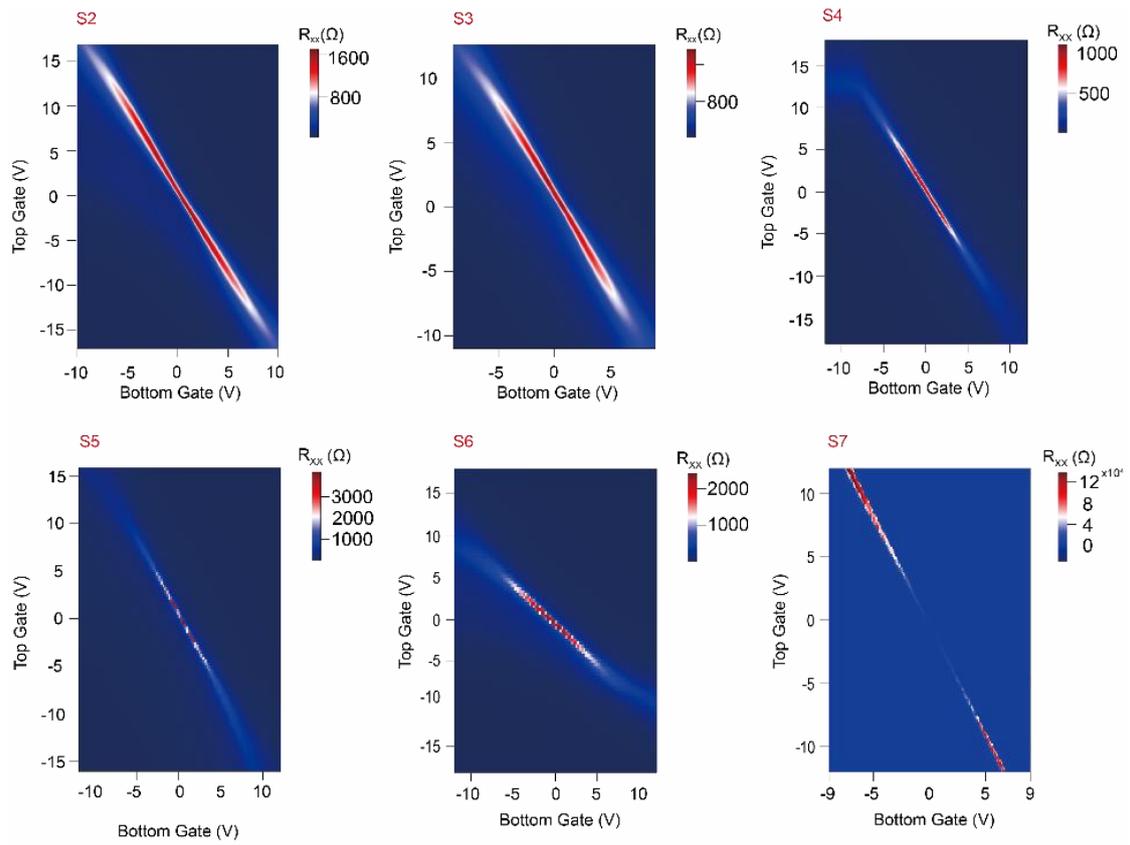
- 1 State Key Laboratory of Quantum Optics and Quantum Optics Devices, Institute of Opto-Electronics, Shanxi University, Taiyuan 030006, China
- 2 Collaborative Innovation Center of Extreme Optics, Shanxi University, Taiyuan 030006, China



**Supplementary Figure S1.** Optical images of the several steps of the fabrication process of sample S1.



**Supplementary Figure S2.** Optical images of samples with the same structure that we fabricated. S1 is the sample mentioned in the main text with ferroelectric polarization, while S2-S7 are samples without ferroelectricity.



**Supplementary Figure S3.** Dual gate mapping of the samples S2-S7 at 40 mK.